



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	30mΩ @ V _G S = 10V	6.2A
30V	42mΩ @ V _{GS} = 4.5V	5.2A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Body Control Electronics
- Power Management Functions
- DC-DC Converters

Features and Benefits

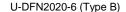
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

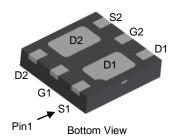
https://www.diodes.com/products/automotive/automotive-products/.

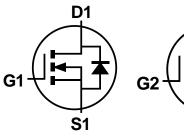
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMN3032LFDBQ</u>)

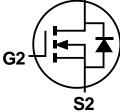
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)









D2

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN3032LFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel		
DMN3032LFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1

U-DFN2020-6 (Type B)



N5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Z		Н	1	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



N5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2012	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	2	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V Steady T _A = +25°C State T _A = +75°C		I _D	6.2 5.0	А	
Maximum Continuous Body Diode Forward Curren	t (Note 6)		ls	2	А
Pulsed Body Diode Forward Current (370µs Pulse	, Duty Cycl	e = 1%)	I _{SM}	20	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 19	%)		I _{DM}	25	А
Avalanche Current (Note 7) L = 0.1mH			las	12	А
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	10	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	р	127	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	RθJA	75	C/VV
Total Power Dissipation (Note 6)		PD	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	р	72	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	43	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	9	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

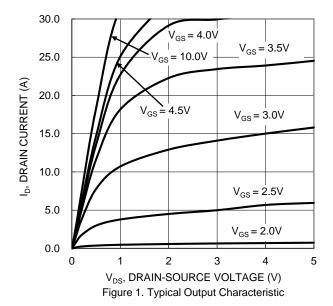
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

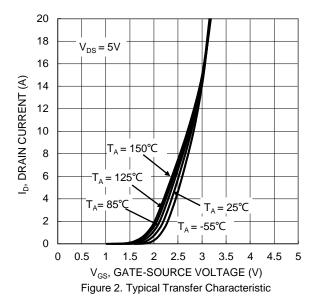
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)			-			
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1.0	μΑ	V _{DS} = 30V, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	_	_	100	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	VGS(TH)	1.0	1.5	2.0	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	Descent	_	25	30	mΩ	$V_{GS} = 10V, I_{D} = 5.8A$
Static Drain-Source On-Resistance	RDS(ON)	_	30	42	11122	$V_{GS} = 4.5V, I_D = 4.8A$
Diode Forward Voltage	VsD	_	0.75	1.2	V	V _G S = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	500		pF	\\ 45\\\\\ 0\\
Output Capacitance	Coss	_	52	_	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	44	_	pF	1 = 1.01/11 12
Gate Resistance	Rg	_	2.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	5.0	_	nC	
Total Gate Charge (V _{GS} = 10V)	Qg	_	10.6	_	nC	\/ 45\/ I- 50A
Gate-Source Charge	Qgs	_	1.3	_	nC	$V_{DS} = 15V, I_{D} = 5.8A$
Gate-Drain Charge	Q_{gd}	_	1.8	_	nC	
Turn-On Delay Time	td(on)	_	2.2	_	ns	
Turn-On Rise Time	t _R	_	2.6	_	ns	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	tD(OFF)	_	9.7	_	ns	$R_L = 2.6\Omega$, $R_G = 3\Omega$
Turn-Off Fall Time	tF	_	2.0	_	ns	

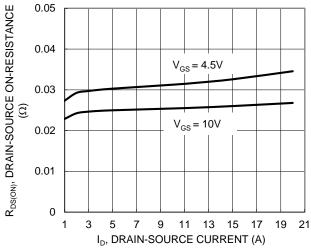
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect. Notes:

^{9.} Guaranteed by design. Not subject to product testing.









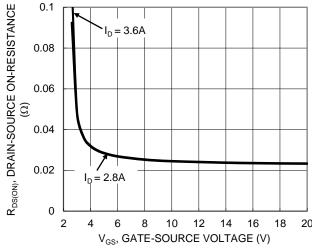
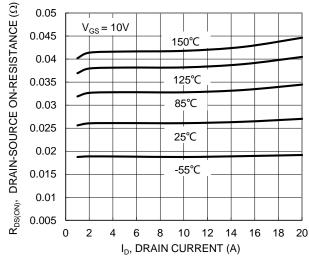


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

Figure 4. Typical Transfer Characteristic



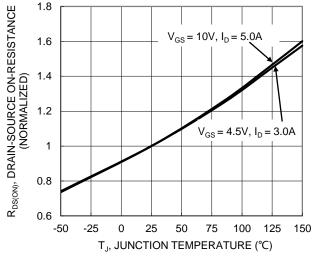


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

Figure 6. On-Resistance Variation with Temperature



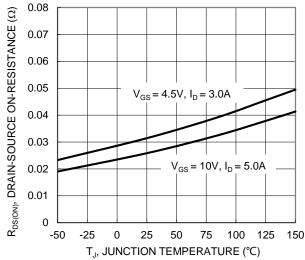
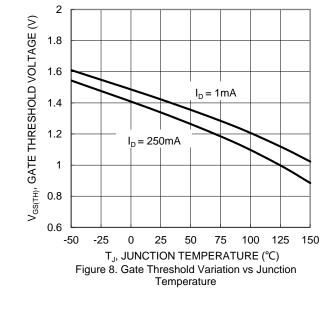


Figure 7. On-Resistance Variation with Temperature



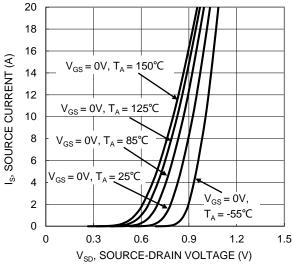
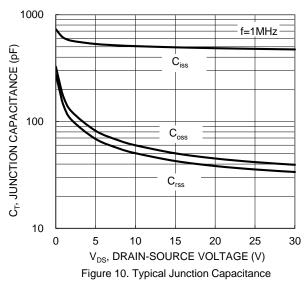
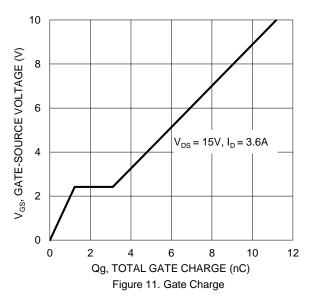
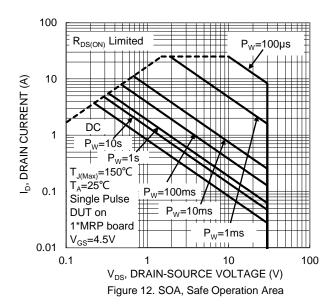


Figure 9. Diode Forward Voltage vs. Current









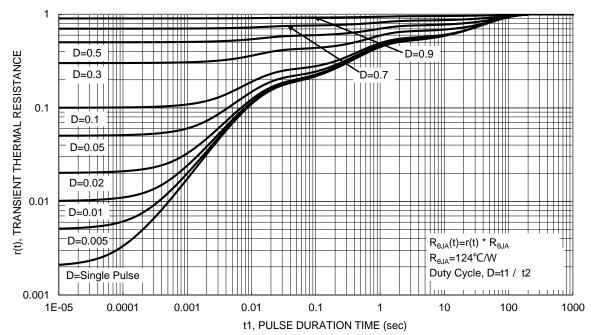
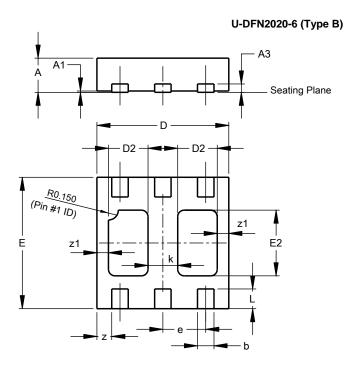


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

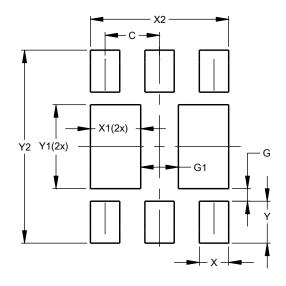


	U-DFN2020-6 Type B							
Dim	Min	Max	Тур					
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	-	-	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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